

Part Number	Customer
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Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	627.00 +/- 11.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Global Flatness (TIR)	<3.00 μ m	ADE 100%
	8.0	Bow	<75.00 μ m	ADE to ASTM F534, 20%
	9.0	Warp	<75.00 μ m	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	7mm	
HandleSilicon	12.0	Handle Growth Method	CZ or FZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	600.00 +/- 10.00 μ m	ADE, 100% - pre oxidation
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Polished Prior to oxidation. Thermal oxide remains on back. Some scratches acceptable with laser marking	Wafer Vendor
	BuriedOxide	19.0	Oxide Type	Thermal
20.0		Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
21.0		Oxide formed on	Handle Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Oxygen Concentration	< 8E17 cm-3	Wafer Vendor
	24.0	Carbon Concentration	< 2E16 cm-3	Wafer Vendor
	25.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	26.0	Nominal Thickness	25.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note 3)
	27.0	Distance to device silicon edge from wafer edge	<= 1.5mm	Typical by Process
	28.0	Device Doping Type	N	Wafer Vendor
	29.0	Device Dopant	Phosphorous	Wafer Vendor
	30.0	Device Resistivity	1- 10 Ohmcm	Wafer Vendor
	31.0	Buried Layer Implant	none	implant vendor
	32.0	Voids	0	Bright Light, 100% (note 2)
	33.0	Scratches	<25mm total length	Bright Light, 100% (note 2)
	34.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information